THYRISTOR-BASED SRAM

ABSTRACT

An integrated circuit structure includes a semiconductor substrate and a thyristor formed thereon. The thyristor has at least four layers, with three P-N junctions therebetween. At least two of the layers are formed horizontally and at least two of the layers are formed vertically. A gate is formed adjacent at least one of the vertically formed layers. An access transistor is formed on the semiconductor substrate, and an interconnect is formed between the thyristor and the access transistor.

FIGURE 8